Minoru Tachiki

List of Publications by Year
in descending order

103	2,060	218677	254184
papers	citations	26 h-index	43 g-index

103	103	103	1765
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Crystal analysis of grain boundaries in boron-doped diamond superconducting quantum interference devices operating above liquid helium temperature. Carbon, 2021, 181, 379-388.	10.3	2
2	Observation of intermediate mixed state in high-purity cavity-grade Nb by magneto-optical imaging. Physical Review B, 2021, 104, .	3.2	12
3	Low-Temperature Properties of the Magnetic Sensor with Amorphous Wire. Sensors, 2020, 20, 6986.	3.8	2
4	Geometrical matching and its influence on the melting transition of confined vortices in a mesoscopic triangle of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Bi</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mrow><mml:mn>8</mml:mn><mml:mo>+</mml:mo><mml:mi>y</mml:mi></mml:mrow></m Physical Review B, 2019, 100, .	3.2	0
5	Single-crystalline boron-doped diamond superconducting quantum interference devices with regrowth-induced step edge structure. Scientific Reports, 2019, 9, 15214.	3.3	7
6	Flattened remnant-field distribution in superconducting bilayer. Physica C: Superconductivity and Its Applications, 2019, 567, 1253489.	1.2	4
7	Synthesis of InSn alloy superconductor below room temperature. Physica C: Superconductivity and Its Applications, 2019, 563, 33-35.	1.2	4
8	Vortex states in a submicron Bi2212 crystal probed by intrinsic Josephson junctions. Journal of Physics: Conference Series, 2018, 969, 012034.	0.4	1
9	Preparation of Magnetic Flux Transformer by Using RE123 High-T_c Superconductor for Low Frequency Electromagnetic Evaluation of Deep-Lying Defects. IEEJ Transactions on Sensors and Micromachines, 2018, 138, 449-454.	0.1	1
10	Vortex states in micron-sized Bi2Sr2CaCu2O8+ycrystals. Journal of Physics: Conference Series, 2017, 871, 012019.	0.4	0
11	Vortex Penetrations in Parallel-connected two Stacks of Intrinsic Josephson Junctions. Physics Procedia, 2016, 81, 85-88.	1.2	0
12	Scanning tunneling microscopy and spectroscopy study of the patchwork structure in Pt doped IrTe2. Physica C: Superconductivity and Its Applications, 2016, 530, 35-37.	1.2	1
13	Size Dependence of Individual Vortex Penetration into Intrinsic Josephson Junction Stacks of Bi2Sr2CaCu2O8+y. Physics Procedia, 2015, 65, 109-112.	1.2	3
14	Visualizing the Pt Doping Effect on Surface and Electronic Structure in Ir_{1â¯'}_xPt_xTe₂ by Scanning Tunneling Microscopy and Spectroscopy. Journal of the Physical Society of Japan, 2015, 84, 043706.	1.6	8
15	Oscillatory Behavior of Vortex-Lattice Melting Transition Line in Mesoscopic<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>Bi</mml:mi></mml:mrow><mml:mrow><mml:mn>2</mml:mn></mml:mrow></m mathvariant="normal">O. Physical Review Letters, 2015, 114, 087001.	7.8	9
16	Examination of Doping Change by C-axis Current Injection in Bi2Sr2CaCu2O8+y and the Influence on Vortex States. Physics Procedia, 2014, 58, 110-113.	1.2	0
17	Fabrication of YBCO-LSMO-YBCO Lateral Structure with AFM Lithography. Physics Procedia, 2014, 58, 195-199.	1.2	2
18	Vortex States of Exfoliated Bi2Sr2CaCu2O8+y Thin Films with and without Micro-Hole Array. Physics Procedia, 2013, 45, 125-128.	1.2	0

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19	Josephson Current in Superconductor-ferromagnet Structure with YBCO-LSMO. Physics Procedia, 2013, 45, 201-204.	1.2	0
20	Fine Probe for an STM-SQUID Probe Microscope. IEEE Transactions on Applied Superconductivity, 2013, 23, 1601804-1601804.	1.7	7
21	Visualizing the effect of structural supermodulation on electronic structure of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow><mml:mi mathvariant="normal">IrTe</mml:mi></mml:mrow><mml:mn>2</mml:mn></mml:msub></mml:math>by scanning tunneling spectroscopy. Physical Review B, 2013, 88, .	3.2	20
22	Highâ€“Resolution Magnetic Field Measurement Using an STMâ€“SQUID. Physics Procedia, 2012, 36, 300-305.	1.2	3
23	Evaluation of an STM-SQUID Probe Microscope. IEEE Transactions on Applied Superconductivity, 2011, 21, 420-423.	1.7	6
24	Coupling GIS and LCA for biodiversity assessments of land use. International Journal of Life Cycle Assessment, 2010, 15, 692-703.	4.7	70
25	Microwave responses on locally modified Bi2Sr2CaCu2O8+Î´ by near-field microwave microscope. Physica C: Superconductivity and Its Applications, 2010, 470, S1021-S1022.	1.2	0
26	STM-SQUID Probe Microscope Based on an RF SQUID Magnetometer. IEEE Transactions on Applied Superconductivity, 2009, 19, 874-877.	1.7	11
27	Highly sensitive anisotropic magnetoresistance magnetometer for Eddy-current nondestructive evaluation. Review of Scientific Instruments, 2009, 80, 036102.	1.3	31
28	Superconducting Properties and Microstructures of ${m MgB}_{2}$ Thin Films Fabricated With the Precursor and Post-Annealing Method. IEEE Transactions on Applied Superconductivity, 2009, 19, 2823-2826.	1.7	2
29	N-14 NQR using a high-T_crf SQUID with a normal metal transformer. Superconductor Science and Technology, 2008, 21, 015023.	3.5	7
30	Detecting the $^{14}{m N}$ NQR Signal Using a High-Tc SQUID. IEEE Transactions on Applied Superconductivity, 2007, 17, 843-845.	1.7	4
31	Development of NQR explosive detector in Japan. , 2007, , .		2
32	STM-SQUID probe microscope. Superconductor Science and Technology, 2007, 20, S374-S379.	3.5	13
33	SQUID Probe Microscope Combined With Scanning Tunneling Microscope. IEEE Transactions on Applied Superconductivity, 2007, 17, 792-795.	1.7	7
34	14N nuclear quadrupole resonance ofp-nitrotoluene using a high-Tcrf SQUID. Superconductor Science and Technology, 2007, 20, 232-234.	3.5	1
35	Superconducting properties of homoepitaxial CVD diamond. Diamond and Related Materials, 2007, 16, 911-914.	3.9	104
36	Sensing of chemical substances using SQUID-based nuclear quadrupole resonance. Physica C: Superconductivity and Its Applications, 2007, 463-465, 1034-1037.	1.2	0

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37	Atomic Force Microscope Based Lithography of YBa2Cu3O7-ÎThin Films. Japanese Journal of Applied Physics, 2006, 45, 5742-5745.	1.5	4
38	Improving the sensitivity of a high-TcSQUID at MHz frequency using a normal metal transformer. Superconductor Science and Technology, 2006, 19, S231-S234.	3.5	9
39	High-TC rf superconducting quantum interference device readout with a cryogenic preamplifier. Review of Scientific Instruments, 2006, 77, 066106.	1.3	0
40	Characterization of locally modified diamond surface using Kelvin probe force microscope. Surface Science, 2005, 581, 207-212.	1.9	58
41	Superconductivity in polycrystalline diamond thin films. Diamond and Related Materials, 2005, 14, 1936-1938.	3.9	72
42	An electron-spectroscopic view of CVD diamond surface conductivity. Diamond and Related Materials, 2005, 14, 459-465.	3.9	12
43	Large-Area Synthesis of Carbon Nanofibers by Low-Power Microwave Plasma-Assisted CVD. Chemical Vapor Deposition, 2004, 10, 125-128.	1.3	21
44	Sample vibration technique for HTS SQUID microscope. Physica C: Superconductivity and Its Applications, 2004, 412-414, 1501-1505.	1.2	0
45	Superconductivity in diamond thin films well above liquid helium temperature. Applied Physics Letters, 2004, 85, 2851-2853.	3.3	277
46	Electron-spectroscopy and -diffraction study of the conductivity of CVD diamond ()2Ã—1 surface. Surface Science, 2003, 529, 180-188.	1.9	9
47	Clâ¯ sensitive biosensor used electrolyte-solution-gate diamond FETs. Biosensors and Bioelectronics, 2003, 19, 137-140.	10.1	44
48	Diamond nanofabrication and characterization for biosensing application. Physica Status Solidi A, 2003, 199, 39-43.	1.7	28
49	Ozone-treated channel diamond field-effect transistors. Diamond and Related Materials, 2003, 12, 1971-1975.	3.9	55
50	High performance diamond MISFETs using CaF2 gate insulator. Diamond and Related Materials, 2003, 12, 399-402.	3.9	29
51	Effect of iodide ions on the hydrogen-terminated and partially oxygen-terminated diamond surface. Diamond and Related Materials, 2003, 12, 618-622.	3.9	35
52	Deep sub-micron gate diamond MISFETs. Diamond and Related Materials, 2003, 12, 1814-1818.	3.9	11
53	Initial growth of heteroepitaxial diamond on Ir (001)/MgO (001) substrates using antenna-edge-type microwave plasma assisted chemical vapor deposition. Diamond and Related Materials, 2003, 12, 246-250.	3.9	27
54	Non-linear increases in excitonic emission in synthetic type-IIa diamond. Diamond and Related Materials, 2003, 12, 1995-1998.	3.9	5

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55	Fabrication of diamond in-plane-gated field effect transistors using oxygen plasma etching. Diamond and Related Materials, 2003, 12, 408-412.	3.9	6
56	Control wettability of the hydrogen-terminated diamond surface and the oxidized diamond surface using an atomic force microscope. Diamond and Related Materials, 2003, 12, 560-564.	3.9	85
57	Cryogenic operation of surface-channel diamond field-effect transistors. Diamond and Related Materials, 2003, 12, 1800-1803.	3.9	8
58	Cathodoluminescence and Hall-effect measurements in sulfur-doped chemical-vapor-deposited diamond. Applied Physics Letters, 2003, 82, 2074-2076.	3.3	26
59	Vibronic Mechanism of High Tc Superconductivity. International Journal of Modern Physics B, 2003, 17, 3266-3270.	2.0	5
60	Development of a Remote Nuclear Quadrupole Resonance Detector. Japanese Journal of Applied Physics, 2003, 42, L1481-L1482.	1.5	4
61	Fabrication of single-hole transistors on hydrogenated diamond surface using atomic force microscope. Applied Physics Letters, 2002, 81, 2854-2856.	3.3	36
62	Effect of Cl-Ionic Solutions on Electrolyte-Solution-Gate Diamond Field-Effect Transistors. Japanese Journal of Applied Physics, 2002, 41, 2595-2597.	1.5	20
63	RF Performance of High Transconductance and High-Channel-Mobility Surface-Channel Polycrystalline Diamond Metal-Insulator-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2002, 41, 2611-2614.	1.5	24
64	Investigation of Current-Voltage Characteristics of Oxide Region Induced by Atomic Force Microscope on Hydrogen-Terminated Diamond Surface. Japanese Journal of Applied Physics, 2002, 41, 4980-4982.	1.5	10
65	Nanoscale Modification of the Hydrogen-Terminated Diamond Surface Using Atomic Force Microscope. Japanese Journal of Applied Physics, 2002, 41, 4983-4986.	1.5	10
66	Low-temperature operation of diamond surface-channel field-effect transistors. Materials Research Society Symposia Proceedings, 2002, 719, 551.	0.1	0
67	RF performance of diamond MISFETs. IEEE Electron Device Letters, 2002, 23, 121-123.	3.9	22
68	Fabrication of heteroepitaxial diamond thin films on Ir(001)/MgO(001) substrates using antenna-edge-type microwave plasma-assisted chemical vapor deposition. Diamond and Related Materials, 2002, 11, 478-481.	3.9	10
69	Fabrication of diamond single-hole transistors using AFM anodization process. Diamond and Related Materials, 2002, 11, 387-391.	3.9	30
70	DC and RF characteristics of 0.7-Î¼m-gate-length diamond metalâ€“insulatorâ€“semiconductor field effect transistor. Diamond and Related Materials, 2002, 11, 378-381.	3.9	24
71	Development of prominent PLD (Aurora method) suitable for high-quality and low-temperature film growth. Applied Surface Science, 2002, 197-198, 294-303.	6.1	46
72	Heteroepitaxial diamond thin film growth on Ir(001)/MgO(001) substrate by antenna-edge plasma assisted chemical vapor deposition. Journal of Crystal Growth, 2002, 237-239, 1277-1280.	1.5	5

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73	High-Tc Superconductivity Driven by Overscreening of Coulomb Interaction. Journal of Superconductivity and Novel Magnetism, 2002, 15, 643-650.	0.5	1
74	Potential applications of surface channel diamond field-effect transistors. Diamond and Related Materials, 2001, 10, 1743-1748.	3.9	33
75	High-frequency performance of diamond field-effect transistor. IEEE Electron Device Letters, 2001, 22, 390-392.	3.9	91
76	Nanodevice fabrication on hydrogenated diamond surface using atomic force microscope. Materials Research Society Symposia Proceedings, 2001, 675, 1.	0.1	3
77	Fabrication of 0.1 Âµm channel diamond Metal-Insulator-Semiconductor Field-Effect Transistor. Materials Research Society Symposia Proceedings, 2001, 680, 1.	0.1	3
78	Optimized NdBa2Cu3Oy thin films deposited by eclipsed pulsed laser ablation. Physica C: Superconductivity and Its Applications, 2001, 356, 205-211.	1.2	6
79	High-Performance Surface-Channel Diamond Field-Effect Transistors. Materials Science Forum, 2001, 353-356, 815-0.	0.3	0
80	Estimation of trap levels in SrTiO3 epitaxial films from measurement of (LaSr)MnO3/SrTiO3/(LaSr)TiO3p-i-ndiode characteristics. Journal of Applied Physics, 2001, 90, 187-191.	2.5	29
81	Excitonic recombination radiation in phosphorus-doped CVD diamonds. Physical Review B, 2001, 64, .	3.2	21
82	An improved laser ablation method using a shadow mask (eclipse method). Electrical Engineering in Japan (English Translation of Denki Gakkai Ronbunshi), 2000, 130, 88-94.	0.4	5
83	Preparation of SrRuO 3 thin film by chemical reactive pulsed laser deposition. Thin Solid Films, 2000, 368, 227-230.	1.8	0
84	Control of adsorbates and conduction on CVD-grown diamond surface, using scanning probe microscope. Applied Surface Science, 2000, 159-160, 578-582.	6.1	32
85	Cu/CaF2/Diamond Metal-Insulator-Semiconductor Field-Effect Transistor Utilizing Self-Aligned Gate Fabrication Process. Japanese Journal of Applied Physics, 2000, 39, L908-L910.	1.5	32
86	Nanofabrication on Hydrogen-Terminated Diamond Surfaces by Atomic Force Microscope Probe-Induced Oxidation. Japanese Journal of Applied Physics, 2000, 39, 4631-4632.	1.5	44
87	Room-Temperature Heteroepitaxial Growth of NiO Thin Films using Pulsed Laser Deposition. Japanese Journal of Applied Physics, 2000, 39, 1817-1820.	1.5	68
88	Manipulation of Laser Ablation Plume by Magnetic Field Application. Japanese Journal of Applied Physics, 1999, 38, 3642-3645.	1.5	40
89	First Demonstration of Rectifying Property ofP-I-NHeterojunctions Fabricated by Tri-Layered Semiconducting Oxides. Japanese Journal of Applied Physics, 1999, 38, 2675-2678.	1.5	101
90	Excimer-laser ablation of RuO2 observed by a streak camera. Journal of Applied Physics, 1999, 85, 2402-2407.	2.5	5

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91	SrTiO3 films epitaxially grown by eclipse pulsed laser deposition and their electrical characterization. Journal of Applied Physics, 1998, 83, 5351-5357.	2.5	36
92	Band Diagram of Metal-Insulator-Magnetic Semiconductor (La0.85Sr0.15MnO3) Structure at Room Temperature. Japanese Journal of Applied Physics, 1998, 37, L999-L1001.	1.5	23
93	<title>Deposition and properties of PLD grown RuO2 thin film</title>. , 1998, 3175, 331.		5
94	<title>Advanced pulsed laser deposition method (eclipse angle)</title>. , 1998, 3175, 347.		2
95	Growth of $f RuO_{2}$ Thin Films on a MgO Substrate by Pulsed Laser Deposition Method. Japanese Journal of Applied Physics, 1997, 36, L511-L514.	1.5	7
96	Advanced eclipse pulsed laser deposition method for growth of perovskite crystals and relatives. Nuclear Instruments & Methods in Physics Research B, 1997, 121, 412-414.	1.4	5
97	Thin film growth of SrBiTiO system by PLD method and optical characterization. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 41, 131-133.	3.5	6
98	Pt/SrBi4Ti4O15/Si-MOS system: preliminary study employing an inverted MOS configuration. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 41, 174-177.	3.5	1
99	Optical Characterization of $f Sr_{inmbi{m}-3}Bi_{4}Ti_{inmbi{m}}O_{3inmbi{m}+3}$ (m=4, 5, 6) Thin Films Grown by Pulsed Laser Deposition Method. Japanese Journal of Applied Physics, 1996, 35, L719-L721.	1.5	20
100	Heteroepitaxial Growth of $f SrBi_{4}Ti_{4}O_{15}/Bi_{2}Sr_{2}CuO_{6+{inmbi y}}$ Structure by ArF Excimer Laser Ablation. Japanese Journal of Applied Physics, 1995, 34, L1145-L1147.	1.5	8
101	Temperature Dependence of Exciton Reflection Spectrain Monoclinic Zinc Diphosphide. Journal of the Physical Society of Japan, 1991, 60, 4351-4356.	1.6	19
102	High frequency application of high transconductance surface-channel diamond field-effect transistors. , 0, , .		1
103	Preparation of a high-T _c superconducting magnetic flux transformer with a 100 mm bore coil and static magnetic field transfer at 77 K.. Japanese Journal of Applied Physics, 0, , .	1.5	2